Docket No.: 57810-075 **PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277

Naoya SOTANI, et al. : Confirmation Number:

Serial No.: : Group Art Unit:

Filed: September 12, 2003 : Examiner: Unknown

For: METHOD OF FABRICATING SEMICONDUCTOR DEVICE AND SYSTEM OF

FABRICATING SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The relevance of each reference listed on attached Form 1449 is discussed in the present specification.

Serial No.:

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

Registration No. 26,106

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Facsimile: (202) 756-8087 **Date: September 12, 2003**

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)					ATTY. DOCKET NO. 57810-075	SERIAL NO.			
					APPLICANT Naoya SOTANI, et al.				
					FILING DATE September 12, 2003	FILING DATE GROUP September 12, 2003			
	<u></u>			U.S. PATEN	T DOCUMENTS				
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EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code2 (# known)		MM-DD-YYYY	Document Document		Relevant Passages or Relevant Figures Appear		
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	i						Yes	No	
			JP 6-345415	12/20/1994	SAMSUNG ELECTRON CO LTD		(Japan w/English Abstract)		
			JP P2001-156017A	06/08/2001	SEMICONDUCTOR ENERGY LAB CO LTD		(Japan w/English Abstract)		
			JP P2002-50576A	02/15/2002	SANYO ELECTRIC CO LTD		(Japan w/English Abstract)		
			JP P2001-291666A	10/19/2001	SANYO ELECTRIC CO LTD		(Japan w/English Abstract)		
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.